RENESAS 4 O/P 1.5V PCIe Gen1-2-3 Clock Generator w/Zo=100ohms

9FGU0441

DATASHEET

Description

The 9FGU0441 is a member of IDT's 1.5V Ultra-Low-Power PCIe clock family with integrated output terminations providing Zo=100 Ω . The device has 4 output enables for clock management, 2 different spread spectrum levels in addition to spread off and 2 selectable SMBus addresses.

Recommended Application

1.5V PCIe Gen1-2-3 clock generator

Output Features

- 4 100MHz Low-Power (LP) HCSL DIF pairs w/Zo=100ohms
- 1 1.5V LVCMOS REF output w/Wake-On-LAN (WOL) support

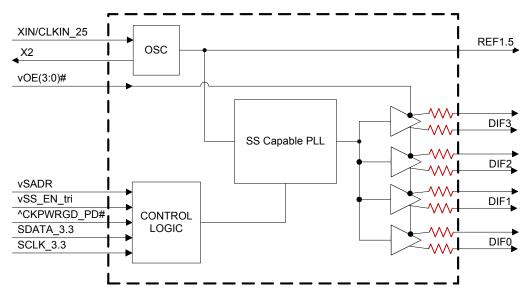
Key Specifications

- DIF cycle-to-cycle jitter <50ps
- DIF output-to-output skew <50ps
- DIF phase jitter is PCIe Gen1-2-3 compliant
- REF phase jitter is < 3.0ps RMS

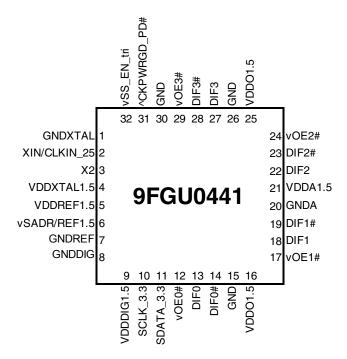
Block Diagram

Features/Benefits

- Direct connection to 100ohm transmission lines; saves 16 resistors compared to standard PCIe devices
- 39mW typical power consumption; reduced thermal concerns
- · OE# pins; support DIF power management
- Programmable Slew rate for each output; allows tuning for various line lengths
- Programmable output amplitude; allows tuning for various application environments
- DIF outputs blocked until PLL is locked; clean system start-up
- Selectable 0%, -0.25% or -0.5% spread on DIF outputs; reduces EMI
- External 25MHz crystal; supports tight ppm with 0 ppm synthesis error
- Configuration can be accomplished with strapping pins; SMBus interface not required for device control
- Selectable SMBus addresses; multiple devices can easily share an SMBus segment
- 3.3V tolerant SMBus interface works with legacy controllers
- Space saving 32-pin 5x5 mm VFQFPN; minimal board space



Pin Configuration



32-pin VFQFPN, 5x5 mm, 0.5mm pitch

^ prefix indicates internal 120KOhm pull up resistor v prefix indicates internal 120KOhm pull down resistor

SMBus Address Selection Table

	SADR	Address	+ Read/Write Bit
State of SADR on first application	0	1101000	Х
of CKPWRGD_PD#	1	1101010	Х

Power Management Table

CKPWRGD PD#	SMBus	DIFx			REF
	OE bit	OEx#	True O/P	Comp. O/P	
0	Х	Х	Low	Low	Hi-Z ¹
1	1	0	Running	Running	Running
1	0	1	Low	Low	Low

1. REF is Hi-Z until the 1st assertion of CKPWRGD_PD# high. After this, when CKPWRG_PD# is low, REF is Low.

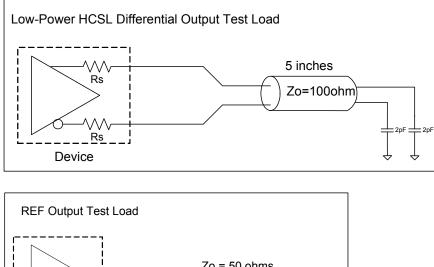
Power Connections

Pin Number		Description
VDD	GND	Description
4	1	XTAL Analog
5	7	REF Output
9	8, 30	Digital Power
16, 25	15, 26	DIF outputs
21	20	PLL Analog

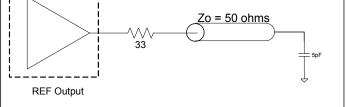
Pin Descriptions

Pin#	Pin Name	Туре	Pin Description
1	GNDXTAL	GND	GND for XTAL
2	XIN/CLKIN_25	IN	Crystal input or Reference Clock input. Nominally 25MHz.
3	Х2	OUT	Crystal output.
4	VDDXTAL1.5	PWR	Power supply for XTAL, nominal 1.5V
5	VDDREF1.5	PWR	VDD for REF output. nominal 1.5V.
6	vSADR/REF1.5	LATCHED I/O	Latch to select SMBus Address/1.5V LVCMOS copy of X1/REFIN pin
7	GNDREF	GND	Ground pin for the REF outputs.
8	GNDDIG	GND	Ground pin for digital circuitry
9	VDDDIG1.5	PWR	1.5V digital power (dirty power)
10	SCLK_3.3	IN	Clock pin of SMBus circuitry, 3.3V tolerant.
11	SDATA_3.3	I/O	Data pin for SMBus circuitry, 3.3V tolerant.
12	vOE0#	IN	Active low input for enabling DIF pair 0. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
13	DIF0	OUT	Differential true clock output
14	DIF0#	OUT	Differential Complementary clock output
15	GND	GND	Ground pin.
16	VDDO1.5	PWR	Power supply for outputs, nominally 1.5V.
17	vOE1#	IN	Active low input for enabling DIF pair 1. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
18	DIF1	OUT	Differential true clock output
19	DIF1#	OUT	Differential Complementary clock output
20	GNDA	GND	Ground pin for the PLL core.
21	VDDA1.5	PWR	1.5V power for the PLL core.
22	DIF2	OUT	Differential true clock output
23	DIF2#	OUT	Differential Complementary clock output
24	vOE2#	IN	Active low input for enabling DIF pair 2. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
25	VDDO1.5	PWR	Power supply for outputs, nominally 1.5V.
26	GND	GND	Ground pin.
27	DIF3	OUT	Differential true clock output
28	DIF3#	OUT	Differential Complementary clock output
29	vOE3#	IN	Active low input for enabling DIF pair 3. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
30	GND	GND	Ground pin.
31	^CKPWRGD_PD#	IN	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pull-up resistor.
32	vSS_EN_tri	LATCHED IN	Latched select input to select spread spectrum amount at initial power up : 1 = -0.5% spread, M = -0.25%, 0 = Spread Off

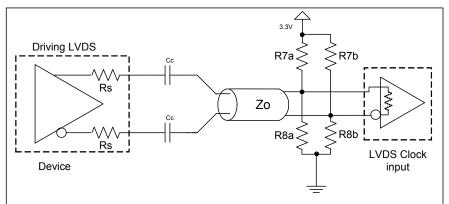
Test Loads



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Alternate Terminations



Driving LVDS inputs

	, ,	Value	
	Receiver has Receiver does not		
Component	termination	have termination	Note
R7a, R7b	10K ohm	140 ohm	
R8a, R8b	5.6K ohm	75 ohm	
Cc	0.1 uF	0.1 uF	
Vcm	1.2 volts	1.2 volts	

Absolute Maximum Ratings

Stresses above the ratings listed below can cause permanent damage to the 9FGU0441. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	МАХ	UNITS	NOTES
Supply Voltage	VDDxx	Applies to all VDD pins	-0.5		2	V	1,2
Input Voltage	V _{IN}		-0.5		V_{DD} +0.5V	V	1,3
Input High Voltage, SMBus	VIHSMB	SMBus clock and data pins			3.3V	V	1
Storage Temperature	Ts		-65		150	°C	1
Junction Temperature	Tj				125	°C	1
Input ESD protection	ESD prot	Human Body Model	2000			V	1

¹Guaranteed by design and characterization, not 100% tested in production.

² Operation under these conditions is neither implied nor guaranteed.

³ Not to exceed 2.5V.

Electrical Characteristics–Current Consumption

TA = T_{AMB:} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
	I _{DDAOP}	VDDA, All outputs active @100MHz		6.2	9	mA	
Operating Supply Current	I _{DDOP}	All VDD, except VDDA and VDDIO, All outputs active @100MHz		21	27	mA	
Wake-on-LAN Current	I _{DDAPD}	VDDA, DIF outputs off, REF output running		0.4	1	mA	2
(CKPWRGD_PD# = '0' Byte 3, bit 5 = '1')	I _{DDPD}	All VDD, except VDDA and VDDIO, DIF outputs off, REF output running		4.5	6.5	mA	2
Powerdown Current (CKPWRGD_PD# = '0'	I _{DDAPD}	VDDA, all outputs off		0.4	1	mA	
Byte 3, bit $5 = 0$	I _{DDPD}	All VDD, except VDDA and VDDIO, all outputs off		0.4	1	mA	

¹ Guaranteed by design and characterization, not 100% tested in production.

² This is the current required to have the REF output running in Wake-on-LAN mode (Byte 3, bit 5 = 1)

Electrical Characteristics–DIF Output Duty Cycle, Jitter, and Skew Characteristics

TA = T_{AMB;} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Duty Cycle	t _{DC}	Measured differentially, PLL Mode	45	50	55	%	1,2
Skew, Output to Output	t _{sk3}	Averaging on, $V_T = 50\%$		32	50	ps	1
Jitter, Cycle to cycle	t _{jcyc-cyc}			16	50	ps	1,2

¹Guaranteed by design and characterization, not 100% tested in production.

² Measured from differential waveform

Electrical Characteristics–Input/Supply/Common Parameters–Normal Operating Conditions

TA = T_{AMB;} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

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PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	VDDxx	Supply voltage for core, analog and single-ended LVCMOS outputs	1.425	1.5	1.575	V	
Ambient Operating	T _{AMB}	Comercial range	0	25	70	°C	
Temperature	' AMB	Industrial range	-40	25	85	°C	
Input High Voltage	V _{IH}	Single-ended inputs, except SMBus	$0.75 V_{DD}$		$V_{DD} + 0.3$	V	
Input Mid Voltage	V _{IM}	Single-ended tri-level inputs ('_tri' suffix)	$0.4 V_{DD}$	$0.5 V_{\text{DD}}$	0.6 V _{DD}	V	
Input Low Voltage	V _{IL}	Single-ended inputs, except SMBus	-0.3		$0.25 V_{DD}$	V	
Output High Voltage	V _{IH}	Single-ended outputs, except SMBus. I _{OH} = -2mA	V _{DD} -0.45			V	
Output Low Voltage	V _{IL}	Single-ended outputs, except SMBus. I _{OL} = -2mA			0.45	V	
	I _{IN}	Single-ended inputs, $V_{IN} = GND$, $V_{IN} = VDD$	-5		5	uA	
Input Current	I _{INP}	Single-ended inputs $V_{IN} = 0 V$; Inputs with internal pull-up resistors $V_{IN} = VDD$; Inputs with internal pull-down resistors	-200		200	uA	
Input Frequency	F _{in}	XTAL, or X1 input	23	25	27	MHz	
Pin Inductance	L _{pin}				7	nH	1
Canaaitanaa	C _{IN}	Logic Inputs, except DIF_IN	1.5		5	pF	1
Capacitance	C _{OUT}	Output pin capacitance			6	pF	1
Clk Stabilization	T _{STAB}	From V _{DD} Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock			1.8	ms	1,2
SS Modulation Frequency	f _{MOD}	Triangular Modulation	30	31.6	33	kHz	1
OE# Latency	t _{LATOE#}	DIF start after OE# assertion DIF stop after OE# deassertion	1		3	clocks	1,3
Tdrive_PD#	t _{DRVPD}	DIF output enable after PD# de-assertion			300	us	1,3
Tfall	t _F	Fall time of single-ended control inputs			5	ns	2
Trise	t _R	Rise time of single-ended control inputs			5	ns	2
SMBus Input Low Voltage	VILSMB				0.6	V	
SMBus Input High Voltage	VIHSMB	V_{DDSMB} = 3.3V, see note 4 for V_{DDSMB} < 3.3V	2.1		3.3	V	4
SMBus Output Low Voltage	V _{OLSMB}	@ I _{PULLUP}			0.4	V	
SMBus Sink Current	I _{PULLUP}	@ V _{OL}	4			mA	
Nominal Bus Voltage	V _{DDSMB}		1.425		3.3	V	
SCLK/SDATA Rise Time	t _{RSMB}	(Max VIL - 0.15) to (Min VIH + 0.15)			1000	ns	1
SCLK/SDATA Fall Time	t _{FSMB}	(Min VIH + 0.15) to (Max VIL - 0.15)			300	ns	1
SMBus Operating Frequency	f _{MAXSMB}	Maximum SMBus operating frequency			400	kHz	1

¹ Guaranteed by design and characterization, not 100% tested in production.

² Control input must be monotonic from 20% to 80% of input swing.

³ Time from deassertion until outputs are >200 mV

 4 For V_{DDSMB} < 3.3V, V_{IHSMB} >= 0.8 x V_{DDSMB}

Electrical Characteristics–DIF Low-Power HCSL Outputs

TA = T_{AMB:} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

		, °					
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Slew rate	т.4	Scope averaging on fast setting	1.2	2.4	3.6	V/ns	1,2,3
Siew fale	Trf	Scope averaging on slow setting	0.8	1.7	2.5	V/ns	1,2,3
Slew rate matching	∆Trf	Slew rate matching, Scope averaging on		9	20	%	1,2,4
Voltage High	V _{HIGH}	Statistical measurement on single-ended signal using oscilloscope math function. (Scope	600	750	850	mV	7
Voltage Low	V _{LOW}	averaging on)	-150	26	150		7
Max Voltage	Vmax	Measurement on single ended signal using		763	1150	mV	7
Min Voltage	Vmin	absolute value. (Scope averaging off)	-300	22		mv	7
Vswing	Vswing	Scope averaging off	300	1448		mV	1,2,7
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	250	390	550	mV	1,5,7
Crossing Voltage (var)	∆-Vcross	Scope averaging off		11	140	mV	1,6,7

¹Guaranteed by design and characterization, not 100% tested in production.

² Measured from differential waveform

³ Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V.

⁴ Matching applies to rising edge rate for Clock and falling edge rate for Clock#. It is measured using a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations.

⁵ Vcross is defined as voltage where Clock = Clock# measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

⁶ The total variation of all Vcross measurements in any particular system. Note that this is a subset of Vcross_min/max (Vcross absolute) allowed. The intent is to limit Vcross induced modulation by setting Δ -Vcross to be smaller than Vcross absolute.

⁷ At default SMBus amplitude settings.

Electrical Characteristics–DIF Output Phase Jitter Parameters

TA = T_{AMB}; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	IND. LIMIT	UNITS	Notes
	t _{jphPCleG1}	PCIe Gen 1		27.7	40	86	ps (p-p)	1,2,3,5
	+	PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz		1.0	1.3	3	ps (rms)	1,2,3,5
Phase Jitter, PLL Mode	tjphPCleG2	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		1.9	2.2	3.1	ps (rms)	1,2,3,5
Thase officer, T LL Would	t _{jphPCleG3}	PCIe Gen 3 Common Clock Architecture (PLL BW of 2-4 or 2-5MHz, CDR = 10MHz)		0.4	0.6	1	ps (rms)	1,2,3,5
	t _{jphPCleG3SRn} S	PCIe Gen 3 Separate Reference No Spread (SRnS) (PLL BW of 2-4 or 2-5MHz, CDR = 10MHz)		0.4	0.6	0.7	ps (rms)	1,2,3,5

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² See http://www.pcisig.com for complete specs

³ Sample size of at least 100K cycles. This figures extrapolates to 108ps pk-pk @ 1M cycles for a BER of 1-12.

⁴ Calculated from Intel-supplied Clock Jitter Tool

⁵ Applies to all differential outputs

Electrical Characteristics–REF

TA = T_{AMB;} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

A = T _{AMB} ; Supply Voltages	per normai (operation conditions, dee rest coads for coading of	Julions				
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	Notes
Long Accuracy	ppm	see Tperiod min-max values		0		ppm	1,2
Clock period	T _{period}	25 MHz output		40		ns	2
Rise/Fall Slew Rate	t _{rf1}	Byte 3 = 1F, 20% to 80% of VDDREF	0.3	0.7	1.1	V/ns	1
Rise/Fall Slew Rate	t _{rf1}	Byte 3 = 5F, 20% to 80% of VDDREF	0.5	1.0	1.6	V/ns	1,3
Rise/Fall Slew Rate	t _{rf1}	Byte 3 = 9F, 20% to 80% of VDDREF	0.77	1.3	1.9	V/ns	1
Rise/Fall Slew Rate	t _{rf1}	Byte 3 = DF, 20% to 80% of VDDREF	0.84	1.4	2.0	V/ns	1
Duty Cycle	d _{t1X}	$V_T = VDD/2 V$	45	47.1	55	%	1,4
Duty Cycle Distortion	d _{tcd}	$V_T = VDD/2 V$, when driven by XIN/CLKIN_25 pin	0	2.0	4	%	1,5
Jitter, cycle to cycle	t _{jcyc-cyc}	$V_T = VDD/2 V$		51.2	250	ps	1,4
Noise floor	t _{jdBc1k}	1kHz offset		-126	-105	dBc	1,4
Noise floor	t _{jdBc10k}	10kHz offset to Nyquist		-139	-110	dBc	1,4
Jitter, phase	t _{jphREF}	12kHz to 5MHz		1.11	3	ps (rms)	1,4

¹Guaranteed by design and characterization, not 100% tested in production.

² All Long Term Accuracy and Clock Period specifications are guaranteed assuming that REF is trimmed to 25.00 MHz

³ Default SMBus Value

⁴ When driven by a crystal.

⁵ X2 should be floating.

Clock Periods–Differential Outputs with Spread Spectrum Disabled

		Measurement Window								
	Center	1 Clock	1us	0.1s	0.1s	0.1s	1us	1 Clock		
SSC OFF	Freq. MHz	-c2c jitter AbsPer Min	-SSC Short-Term Average Min	- ppm Long-Term Average Min	0 ppm Period Nominal	+ ppm Long-Term Average Max	+SSC Short-Term Average Max	+c2c jitter AbsPer Max	Units	Notes
DIF	100.00	9.94900		9.99900	10.00000	10.00100		10.05100	ns	1,2

Clock Periods–Differential Outputs with -0.5% Spread Spectrum Enabled

			Measurement Window							
	Center	1 Clock	1us	0.1s	0.1s	0.1s	1us	1 Clock		
SSC ON	Freq. MHz	-c2c jitter AbsPer Min	-SSC Short-Term Average Min	- ppm Long-Term Average Min	0 ppm Period Nominal	+ ppm Long-Term Average Max	+SSC Short-Term Average Max	+c2c jitter AbsPer Max	Units	Notes
DIF	99.75	9.94906	9.99906	10.02406	10.02506	10.02607	10.05107	10.10107	ns	1,2

¹Guaranteed by design and characterization, not 100% tested in production.

² All Long Term Accuracy and Clock Period specifications are guaranteed assuming that REF is trimmed to 25.00 MHz

General SMBus Serial Interface Information

How to Write

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) sends the byte count = X
- IDT clock will acknowledge
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time
- Controller (host) sends a Stop bit

	Index Blo	ock \	Write Operation
Controll	er (Host)		IDT (Slave/Receiver)
Т	starT bit		
Slave A	Address		
WR	WRite		
			ACK
Beginning	g Byte = N		
			ACK
Data Byte	Count = X	_	
			ACK
Beginnin	g Byte N	_	
		_	ACK
0		\times	
0		X Byte	0
0		Ð	0
			0
Byte N	+ X - 1		
			ACK
Р	stoP bit		

Note: Read/Write address is determined by SADR latch.

How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X_(H) was written to Byte 8)
- · Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

	Index Block F	Read C	Operation
Co	ntroller (Host)	_	IDT (Slave/Receiver)
Т	starT bit	_	
S	Slave Address		
WR	WRite	-	
		-	ACK
Begi	nning Byte = N	-	
		-	ACK
RT	Repeat starT	-	
S	ave Address		
RD	ReaD		
			ACK
		_	Data Byte Count=X
	ACK		
		-	Beginning Byte N
	ACK	-	
		te (0
	0	X Byte	0
	0	×	0
	0		
			Byte N + X - 1
Ν	Not acknowledge	-	
Р	stoP bit		

SMBus Table: Output Enable Register

Byte 0	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved			·	1
Bit 6		Reserved				1
Bit 5	Reserved					1
Bit 4	Reserved					1
Bit 3	DIF OE3	Output Enable	RW	Low/Low	Enabled	1
Bit 2	DIF OE3	Output Enable	RW	Low/Low	Enabled	1
Bit 1	DIF OE2	Output Enable	RW	Low/Low	Enabled	1
Bit 0	DIF OE1	Output Enable	RW	Low/Low	Enabled	1

SMBus Table: SS Readback and Vhigh Control Register

Byte 1	Name	Control Function	Туре	0	1	Default
Bit 7	SSENRB1	SS Enable Readback Bit1	R	00' for SS_EN_tri = 0, '01' for SS_EN_tri		Latch
Bit 6	SSENRB1	SS Enable Readback Bit0	R	= 'M', '11 for S	S_EN_tri = '1'	Latch
Bit 5	SSEN_SWCNTRL	Enable SW control of SS	RW	SS control locked	Values in B1[4:3] control SS amount.	0
Bit 4	SSENSW1	SS Enable Software Ctl Bit1	RW ¹	00' = SS Off, '01' = -0.25% SS,		0
Bit 3	SSENSW0	SS Enable Software Ctl Bit0	RW ¹	'10' = Reserved	, '11'= -0.5% SS	0
Bit 2		Reserved				1
Bit 1	AMPLITUDE 1	Controls Output Amplitude	RW	00 = 0.55V	01 = 0.65V	1
Bit 0	AMPLITUDE 0		RW	10= 0.7V	11 = 0.8V	0

1. B1[5] must be set to a 1 for these bits to have any effect on the part.

SMBus Table: DIF Slew Rate Control Register

Byte 2	Name	Control Function	Туре	0	1	Default
Bit 7	Reserved					1
Bit 6	Reserved				1	
Bit 5	Reserved					1
Bit 4	Reserved				1	
Bit 3	SLEWRATESEL DIF3	Adjust Slew Rate of DIF3	RW	Slow Setting	Fast Setting	1
Bit 2	SLEWRATESEL DIF2	Adjust Slew Rate of DIF2	RW	Slow Setting	Fast Setting	1
Bit 1	SLEWRATESEL DIF1	Adjust Slew Rate of DIF3	RW	Slow Setting	Fast Setting	1
Bit 0	SLEWRATESEL DIF0	Adjust Slew Rate of DIF1	RW	Slow Setting	Fast Setting	1

SMBus Table: REF Control Register

Byte 3	Name	Control Function	Туре	0	1	Default
Bit 7	REF	Slew Rate Control	RW	00 = Slowest	01 = Slow	0
Bit 6	Bit 6		RW	10 = Fast	11 = Faster	1
Bit 5	REF Power Down Function	Wake-on-Lan Enable for REF	RW	REF does not run in Power Down	REF runs in Power Down	0
Bit 4	REF OE	REF Output Enable	RW	Low	Enabled	1
Bit 3		Reserved				1
Bit 2		Reserved				1
Bit 1	Reserved					1
Bit 0		Reserved				1

Byte 4 is reserved and reads back 'hFF'.

RENESAS

SMBus Table: Revision and Vendor ID Register

Byte 5	Name	Control Function	Туре	0	1	Default
Bit 7	RID3	Revision ID	R		0	
Bit 6	RID2		R	A rev = 0000		0
Bit 5	RID1		R			0
Bit 4	RID0		R		0	
Bit 3	VID3		R			0
Bit 2	VID2	VENDOR ID	R	0001	0001 = IDT	
Bit 1	VID1		R	10001 – 101		0
Bit 0	VID0		R		1	

SMBus Table: Device Type/Device ID

Byte 6	Name	Control Function	Туре	0	1	Default
Bit 7	Device Type1	Device Type	R	00 = FGx, 01 =	DBx ZDB/FOB,	0
Bit 6	Device Type0	Device Type	R	10 = DMx, 11= DBx FOB		0
Bit 5	Device ID5		R			0
Bit 4	Device ID4		R			0
Bit 3	Device ID3	Device ID	R	000100 binary or 04 hex		0
Bit 2	Device ID2	Device iD	R			1
Bit 1	Device ID1]	R			0
Bit 0	Device ID0		R			0

SMBus Table: Byte Count Register

Byte 7	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				0
Bit 6		Reserved				0
Bit 5		Reserved				0
Bit 4	BC4		RW			0
Bit 3	BC3		RW	Writing to this regist	er will configure how	1
Bit 2	BC2	Byte Count Programming	RW	many bytes will be r	ead back, default is	0
Bit 1	BC1		RW	= 8 b	ytes.	0
Bit 0	BC0		RW			0

Recommended Crystal Characteristics (3225 package)

PARAMETER	VALUE	UNITS	NOTES
Frequency	25	MHz	1
Resonance Mode	Fundamental	-	1
Frequency Tolerance @ 25°C	±20	PPM Max	1
Frequency Stability, ref @ 25°C Over	+20	PPM Max	1
Operating Temperature Range	120	F F IVI IVIAX	1
Temperature Range (commerical)	0~70	°C	1
Temperature Range (industrial)	-40~85	°C	2
Equivalent Series Resistance (ESR)	50	Ω Max	1
Shunt Capacitance (C _O)	7	pF Max	1
Load Capacitance (CL)	8	pF Max	1
Drive Level	0.3	mW Max	1
Aging per year	±5	PPM Max	1

Notes:

1. FOX 603-25-150.

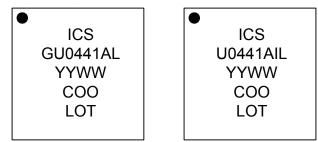
2. For I-temp, FOX 603-25-261.

Thermal Characteristics

PARAMETER	SYMBOL	CONDITIONS	PKG	TYP.	UNITS	NOTES
Thermal Resistance	θ _{JC}	Junction to Case	NLG32	42	°C/W	1
	θ_{Jb}	Junction to Base		2.4	∘C/W	1
	θ _{JA0}	Junction to Air, still air		39	°C/W	1
	θ_{JA1}	Junction to Air, 1 m/s air flow	INLG32	33	∘C/W	1
	θ_{JA3}	Junction to Air, 3 m/s air flow		28	°C/W	1
	θ_{JA5}	Junction to Air, 5 m/s air flow		27	∘C/W	1

¹ePad soldered to board

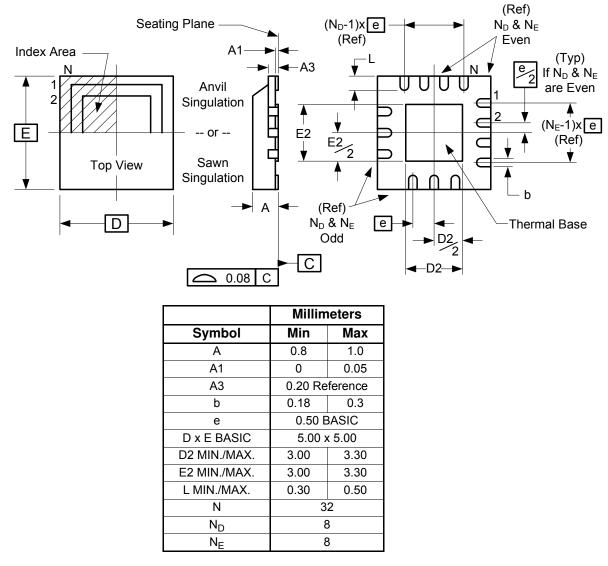
Marking Diagrams



Notes:

- 1. "LOT" is the lot number.
- 2. "COO" denotes the country of origin.
- 3. "YYWW" is the last two digits of the year and week that the part was assembled.
- 4. Line 2: truncated part number.
- 5. "L" denotes RoHS compliant package.
- 6. "I" denotes industrial temperature grade.





Ordering Information

Part / Order Number	Shipping Packaging	Package	Temperature
9FGU0441AKLF	Trays	32-pin VFQFPN	0 to +70° C
9FGU0441AKLFT	Tape and Reel	32-pin VFQFPN	0 to +70° C
9FGU0441AKILF	Trays	32-pin VFQFPN	-40 to +85° C
9FGU0441AKILFT	Tape and Reel	32-pin VFQFPN	-40 to +85° C

"LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

"A" is the device revision designator (will not correlate with the datasheet revision).

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Revision History

Rev.	Issue Date	Intiator	Description	
А	9/24/2014	RDW	 Updated electrical tables with latest versions for release. Updated SMBus nomenclature for consistency with the family. Removed references to Suspend Mode. This is replaced by Power Down with Wake-on-LAN Modes in the current consumption table. Updated GenDes tab for front page consistency. All Electrical tables updated with characterization data. Updated doc with latest template. Move to final. 	Various
В	10/18/2016	RDW	Removed IDT crystal part number	



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